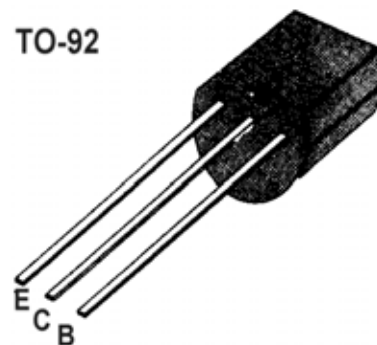


■■ APPLICATION: Frequency Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-6	V
Collector current	I _C	-150	mA
Collector Power Dissipation	I _{CP}	-400	mW
Junction Temperature	P _C	500	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector Cut-off Current	h _{FE1}	160		560		V _{CE} = -6V, I _C = -1mA
	h _{FE2}	70				V _{CE} = -6V, I _C = -0.1mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} = -35V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -4V, I _C =0
Collector-Base Breakdown Voltage	BV _{CB0}	-60			V	I _C = -0.01mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-50			V	I _C = -1mA, R _{BE} =
Emitter-Base Breakdown Voltage	BV _{EBO}	-6			V	I _E = -0.01mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.3	V	I _C = -100mA, I _B = -10mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			-1	V	I _C = -100mA, I _B = -10mA
Gain bandwidth product	f _T		200		MHz	V _{CE} = -6V, I _C = -10mA
Common Base Output Capacitance	C _{ob}		4.5		PF	V _{CB} = -6V, I _E =0, f = 1MHz

■■ h_{FE} Classification

Classification	F	G
h _{FE}	160~320	280~560